

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Currently Amended) A method of growing a gallium nitride single crystal using a flux comprising at least sodium metal[[;]], said method comprising the step of:
growing said gallium nitride single crystal in an atmosphere comprising gas mixture comprising nitrogen gas under a total pressure of 300 atms ~~or higher and 2000~~ to 1200 atms or lower and at a temperature of 850°C to 1200°C, said atmosphere having a nitrogen partial pressure of 120 atms to 600 atms.
2. (Currently Amended) The method of claim 1 ~~8~~, wherein said atmosphere has a nitrogen partial pressure of 100 atms ~~or higher and to 2000 atms or lower~~.
3. (Currently Amended) The method of claim 1 ~~8~~, wherein said crystal is grown at a temperature of 900°C ~~or higher and to 1500°C or lower~~.
4. (Currently Amended) The method of claim 1, wherein said crystal is grown at a temperature of 950°C ~~or higher and to 1200°C or lower~~.
5. (Currently Amended) The method of claim 1, further comprising the step of elevating a crucible containing said flux so that until a seed crystal contacts said flux.
6. (Currently Amended) The method of claim 1, wherein said gallium nitride single crystal is grown using a system for hot isostatic ~~press~~ pressing.
7. (Cancelled).

8. (Currently Amended) A method of growing a gallium nitride single crystal using a flux comprising at least sodium metal~~[[;]]~~, said method comprising ~~the steps of:~~

elevating a crucible containing said flux ~~so that~~ until a seed crystal contacts said flux; and

growing said gallium nitride single crystal in an atmosphere comprising a gas mixture comprising nitrogen gas under a total pressure of 300 atms ~~or higher and to~~ 2000 atms ~~or lower~~.

9. (Currently Amended) The method of claim 8, wherein said crystal is grown at a temperature of 950°C ~~or higher and to~~ 1200°C ~~or lower~~.

10. (Currently Amended) The method of claim 8, wherein said gallium nitride single crystal is grown using a system for hot isostatic ~~press~~ pressing.